

Tae-Yeon Seong

List of Publications by Year in descending order

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253
papers

6,118
citations

71102

41
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91884

69
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256
all docs

256
docs citations

256
times ranked

4771
citing authors

#	ARTICLE	IF	CITATIONS
1	High ultraviolet transparent conducting electrodes formed using tantalum oxide/Ag multilayer. <i>Ceramics International</i> , 2022, 48, 3536-3543.	4.8	2
2	Patterning All-Inorganic Halide Perovskite with Adjustable Phase for High-Resolution Color Filter and Photodetector Arrays. <i>Advanced Functional Materials</i> , 2022, 32, .	14.9	21
3	Modulation of lattice strain in ZnO thin films by ion implantation. <i>Materials Letters</i> , 2022, 314, 131839.	2.6	2
4	Interplay of sidewall damage and light extraction efficiency of micro-LEDs. <i>Optics Letters</i> , 2022, 47, 2250.	3.3	15
5	Inhomogeneous Barrier Height Characteristics of n-Type AlInP for Red AlGaInP-Based Light-Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2022, 11, 035007.	1.8	0
6	Improved performance of deep ultraviolet AlGaIn-based light-emitting diode by reducing contact resistance of Al-based reflector. <i>Journal of Alloys and Compounds</i> , 2022, 910, 164895.	5.5	2
7	An Artificial Tactile Neuron Enabling Spiking Representation of Stiffness and Disease Diagnosis. <i>Advanced Materials</i> , 2022, 34, e2201608.	21.0	20
8	The effect of dry etching condition on the performance of blue micro light-emitting diodes with reduced quantum confined Stark effect epitaxial layer. <i>Journal of Applied Physics</i> , 2022, 131, 153104.	2.5	2
9	Exploring dopant effects in stannic oxide nanoparticles for CO ₂ electro-reduction to formate. <i>Nature Communications</i> , 2022, 13, 2205.	12.8	61
10	SWIR imaging using PbS QD photodiode array sensors. <i>Optics Express</i> , 2022, 30, 20659.	3.4	0
11	Using a NiZn solid solution layer to produce high-barrier height Schottky contact to semipolar (20°-21) n-type GaN. <i>Journal of Alloys and Compounds</i> , 2021, 852, 157003.	5.5	4
12	Improving Performance of GaAs-Based Vertical-Cavity Surface-Emitting Lasers by Employing Thermally Conductive Metal Substrate. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 015001.	1.8	2
13	Using Ag Sinter Paste to Improve the Luminous Flux and Reliability of InGaIn-Based LED Package for Commercial Vehicle Daytime Running Light. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 015004.	1.8	1
14	A Comparison Study on Multilayered Barrier Oxide Structure in Charge Trap Flash for Synaptic Operation. <i>Crystals</i> , 2021, 11, 70.	2.2	5
15	Micro-Light Emitting Diode: From Chips to Applications. <i>Laser and Photonics Reviews</i> , 2021, 15, 2000133.	8.7	108
16	Improved Reliability of 278 nm Deep Ultraviolet AlGaIn-Based Flip-Chip Light Emitting Diodes by Using ITO/Al Contact. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 045002.	1.8	3
17	Improving Emission Uniformity of InGaIn/GaN-Based Vertical LEDs by Using Reflective ITO/Ag n-Contact. <i>Electronics (Switzerland)</i> , 2021, 10, 975.	3.1	1
18	Optimization of Ni/Ag-Based Reflectors to Improve the Performance of 273 nm Deep Ultraviolet AlGaIn-Based Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 045005.	1.8	3

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19	Using Self-Aligned Si Barrier to Enhance the Contrast Ratio and Performance of Pixelated Light Emitting Diode for Vehicle Headlamp. ECS Journal of Solid State Science and Technology, 2021, 10, 045003.	1.8	1
20	Tantalum Doping to Improve Switching Characteristics and Bias Stress Stability of Amorphous Indium-Gallium-Zin Oxide Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2021, 10, 065004.	1.8	0
21	Design of mid-infrared filter array based on plasmonic metal nanodiscs array and its application to on-chip spectrometer. Scientific Reports, 2021, 11, 12218.	3.3	12
22	Stable electrical performance of AlGaInP-based red micro-light emitting diode by controlling interfacial morphologies of metal contacts. Journal of Alloys and Compounds, 2021, 872, 159629.	5.5	5
23	Effects of Current, Temperature, and Chip Size on the Performance of AlGaInP-Based Red Micro-Light-Emitting Diodes with Different Contact Schemes. ECS Journal of Solid State Science and Technology, 2021, 10, 095001.	1.8	12
24	High Field-Effect Mobility Two-Channel InGaZnO Thin-Film Transistors for Low-Voltage Operation. IEEE Transactions on Electron Devices, 2021, 68, 6166-6170.	3.0	1
25	Realization of an Artificial Visual Nervous System using an Integrated Optoelectronic Device Array. Advanced Materials, 2021, 33, e2105485.	21.0	33
26	Realization of an Artificial Visual Nervous System using an Integrated Optoelectronic Device Array (Adv. Mater. 51/2021). Advanced Materials, 2021, 33, .	21.0	3
27	Effect of unevenly-distributed V pits on the optical and electrical characteristics of green micro-light emitting diode. Journal Physics D: Applied Physics, 2020, 53, 045106.	2.8	3
28	Improvement in the Reliability of AlGaInP-Based Light-Emitting Diode Package Using Optimal Silicone and Leadframe Structure. ECS Journal of Solid State Science and Technology, 2020, 9, 015014.	1.8	4
29	Self-catalytic-grown SnO _x nanocones for light outcoupling enhancement in organic light-emitting diodes. Nanotechnology, 2020, 31, 135204.	2.6	3
30	Improvement of The Light Output of Blue InGaN-Based Light Emitting Diodes by Using a Buried Stripe-Typen-Contact and Reflective Bonding Pad. ECS Journal of Solid State Science and Technology, 2020, 9, 015021.	1.8	0
31	Formation of high ultraviolet transparent SrVO _x /Ag-based conducting electrode. Ceramics International, 2020, 46, 19484-19490.	4.8	6
32	Damage-free plasma etching to enhance performance of AlGaInP-based micro-light emitting diode. IEEE Photonics Technology Letters, 2020, , 1-1.	2.5	4
33	Surface passivation of light emitting diodes: From nano-size to conventional mesa-etched devices. Surfaces and Interfaces, 2020, 21, 100765.	3.0	11
34	Forming high transmittance GaSnO/Ag/GaSnO conducting electrodes for optoelectronic devices. Ceramics International, 2020, 46, 28165-28172.	4.8	3
35	Thermally stable AgCu alloy disc array for near infrared filters. Current Applied Physics, 2020, 20, 1321-1327.	2.4	2
36	Improved Leakage and Output Characteristics of Pixelated LED Array for Headlight application. ECS Journal of Solid State Science and Technology, 2020, 9, 045011.	1.8	1

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37	Performance Comparison of InGaN-Based Phosphor Converted and AlGaInP-Based Red Light-Emitting Diode Packages for Vehicle Rear Fog Lamps. ECS Journal of Solid State Science and Technology, 2020, 9, 055003.	1.8	1
38	Improving the Leakage Characteristics and Efficiency of GaN-based Micro-Light-Emitting Diode with Optimized Passivation. ECS Journal of Solid State Science and Technology, 2020, 9, 055001.	1.8	35
39	Optimization of InGaN-based LED Package Structure for Automotive Adaptive Driving Beam Headlamp. ECS Journal of Solid State Science and Technology, 2020, 9, 055017.	1.8	3
40	Effects of Ultraviolet Wavelength and Ambient Temperature on Reliability of Silicones in InAlGaInP-Based Light-Emitting-Diode Package. ECS Journal of Solid State Science and Technology, 2020, 9, 035005.	1.8	2
41	Improved Light Output of AlGaInP-Based Micro-Light Emitting Diode Using Distributed Bragg Reflector. IEEE Photonics Technology Letters, 2020, 32, 438-441.	2.5	11
42	Oblique-Angle Deposited SiO ₂ /Al Omnidirectional Reflector for Enhancing the Performance of AlGaInP-Based Ultraviolet Light-Emitting Diode. ECS Journal of Solid State Science and Technology, 2020, 9, 026005.	1.8	5
43	Using SiO ₂ -Based Distributed Bragg Reflector to Improve the Performance of AlGaInP-Based Red Micro-Light Emitting Diode. ECS Journal of Solid State Science and Technology, 2020, 9, 036002.	1.8	4
44	Sputtering-deposited amorphous SrVOx-based memristor for use in neuromorphic computing. Scientific Reports, 2020, 10, 5761.	3.3	19
45	All-Solution Processed Multicolor Patterning Technique of Perovskite Nanocrystal for Color Pixel Array and Flexible Optoelectronic Devices. Advanced Optical Materials, 2020, 8, 2000501.	7.3	23
46	Heavy Mg Doping to Form Reliable Rh Reflective Ohmic Contact for 278 nm Deep Ultraviolet AlGaInP-Based Light-Emitting Diodes. ECS Journal of Solid State Science and Technology, 2020, 9, 065016.	1.8	6
47	Selective Coating of White Silicone to Improve the Optical and Thermal Characteristics of White LED Packages. ECS Journal of Solid State Science and Technology, 2020, 9, 065008.	1.8	0
48	Effect of the Surface Morphology of Plated Printed Circuit Board on the Reliability of LED Packages. ECS Journal of Solid State Science and Technology, 2020, 9, 065018.	1.8	0
49	Ag-Pd-Cu alloy reflector to improve the opto-electrical performance and electromigration resistance of near ultraviolet GaN-based light-emitting diode. Journal of Alloys and Compounds, 2019, 800, 512-517.	5.5	11
50	Hole injection mechanism in the quantum wells of blue light emitting diode with V pits for micro-display application. Applied Physics Express, 2019, 12, 102016.	2.4	6
51	Via-Hole-Type Flip-Chip Packaging to Improve the Thermal Characteristics and Reliability of Blue Light Emitting Diodes. ECS Journal of Solid State Science and Technology, 2019, 8, Q165-Q170.	1.8	5
52	Combined effects of oxygen pressures and RF powers on the electrical characteristics of ITO-based multilayer transparent electrodes. Vacuum, 2019, 169, 108871.	3.5	8
53	Using Ag disc array to tune infrared transmittance of ITO-based multilayer films. Journal of Alloys and Compounds, 2019, 785, 742-746.	5.5	4
54	Combined effects of V pits and chip size on the electrical and optical properties of green InGaN-based light-emitting diodes. Journal of Alloys and Compounds, 2019, 796, 146-152.	5.5	28

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55	The emergence and prospects of deep-ultraviolet light-emitting diode technologies. <i>Nature Photonics</i> , 2019, 13, 233-244.	31.4	800
56	Optimization of tunable guided-mode resonance filter based on refractive index modulation of graphene. <i>Scientific Reports</i> , 2019, 9, 19951.	3.3	14
57	Solid-State Carbon-Doped GaN Schottky Diodes by Controlling Dissociation of the Graphene Interlayer with a Sputtered AlN Capping Layer. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 48086-48094.	8.0	4
58	Forming ITO/Ag Hole-Array/ITO Multilayers for Near Infrared Transparent Conducting Electrodes and Filters. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q189-Q193.	1.8	1
59	Plasma and Annealing Treatments to Form Height-Barrier Ni-Based Schottky Contact to n-GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q194-Q199.	1.8	4
60	Optimized ITO/Ag/ITO multilayers as a current spreading layer to enhance the light output of ultraviolet light-emitting diodes. <i>Journal of Alloys and Compounds</i> , 2019, 776, 960-964.	5.5	41
61	Inhomogeneity of barrier heights of transparent Ag/ITO Schottky contacts on n-type GaN annealed at different temperatures. <i>Journal of Alloys and Compounds</i> , 2018, 742, 66-71.	5.5	4
62	Interfacial reactions to form high-barrier-height ITO-based Schottky contacts on p-type GaN using a Ti interlayer. <i>Journal of Alloys and Compounds</i> , 2018, 741, 999-1005.	5.5	4
63	An Optically Flat Conductive Outcoupler Using Core/Shell Ag/ZnO Nanochurros. <i>Small</i> , 2018, 14, e1800056.	10.0	8
64	The effects of film thickness on the electrical, optical, and structural properties of cylindrical, rotating, magnetron-sputtered ITO films. <i>Applied Surface Science</i> , 2018, 440, 1211-1218.	6.1	59
65	High-performance GaN-based light emitting diodes grown on 8-inch Si substrate by using a combined low-temperature and high-temperature-grown AlN buffer layer. <i>Journal of Alloys and Compounds</i> , 2018, 732, 630-636.	5.5	22
66	Flexible ITO films with atomically flat surfaces for high performance flexible perovskite solar cells. <i>Nanoscale</i> , 2018, 10, 20587-20598.	5.6	58
67	Light output performance of red AlGaInP-based light emitting diodes with different chip geometries and structures. <i>Optics Express</i> , 2018, 26, 11194.	3.4	135
68	Improved angular color uniformity and hydrothermal reliability of phosphor-converted white light-emitting diodes by using phosphor sedimentation. <i>Optics Express</i> , 2018, 26, 28634.	3.4	9
69	Review of Group III-Nitride-Based Ultraviolet Light-Emitting Diodes: Ways of Increasing External Quantum Efficiency. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, Q42-Q52.	1.8	81
70	Ag nanowire-based electrodes for improving the output power of ultraviolet AlGaIn-based light-emitting diodes. <i>Journal of Alloys and Compounds</i> , 2017, 703, 198-203.	5.5	13
71	Improved light output power of GaN-based ultraviolet light-emitting diode using a mesh-type GaN/SiO ₂ /Al omnidirectional reflector. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600789.	1.8	2
72	Electrical and optical characteristics of transparent conducting Si-doped ZnO/hole-patterned Ag/Si-doped ZnO multilayer films. <i>Ceramics International</i> , 2017, 43, 3693-3697.	4.8	6

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73	Electron Transport Layer-Free Inverted Organic Solar Cells Fabricated with Highly Transparent Low-Resistance Indium Gallium Zinc Oxide/Ag/Indium Gallium Zinc Oxide Multilayer Electrode. <i>Journal of Electronic Materials</i> , 2017, 46, 2140-2146.	2.2	4
74	Reducing forward voltage and enhancing output performance of InGaN-based blue light-emitting diodes using metal dot-embedded transparent p-type finger. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600792.	1.8	3
75	Using agglomerated Ag grid to improve the light output of near ultraviolet AlGaN-based light-emitting diode. <i>Microelectronic Engineering</i> , 2017, 169, 29-33.	2.4	7
76	Improvement of the light output of AlGaInP-based light-emitting diode by employing highly transparent Au/ITO p-type electrode. <i>Journal of Alloys and Compounds</i> , 2017, 699, 1180-1185.	5.5	2
77	Inverted Organic Solar Cells Fabricated with Room-Temperature-Deposited Transparent Multilayer Electrodes. <i>Bulletin of the Korean Chemical Society</i> , 2017, 38, 856-860.	1.9	1
78	A Thermally Stable NiZn/Ta/Ni Scheme to Replace AuBe/Au Contacts in High-Efficiency AlGaInP-Based Light-Emitting Diodes. <i>Journal of Electronic Materials</i> , 2017, 46, 4750-4754.	2.2	0
79	Transparent Conductive ITO/Ag/ITO Electrode Deposited at Room Temperature for Organic Solar Cells. <i>Journal of Electronic Materials</i> , 2017, 46, 306-311.	2.2	24
80	Cr/ITO semi-transparent n-type electrode for high-efficiency AlGaN/InGaN-based near ultraviolet light-emitting diodes. <i>Superlattices and Microstructures</i> , 2017, 111, 872-877.	3.1	2
81	Effect of Amine Additive for the Synthesis of Cadmium Selenide Quantum Dots in a Microreactor. <i>International Journal of Applied Ceramic Technology</i> , 2016, 13, 223-227.	2.1	6
82	InGaN-Based Light-Emitting Diodes Grown on a Micro/Nanoscale Hybrid Patterned Sapphire Substrate. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 34520-34529.	8.0	25
83	Controlling the defect density to improve the output power of InGaN/GaN-based vertical light-emitting diodes by using substrates patterned with SiO ₂ lenses. <i>Philosophical Magazine</i> , 2016, 96, 2919-2929.	1.6	2
84	Thermally stable AuBe-based ohmic contacts to p-type GaP for AlGaInP-based light-emitting diode by using a tungsten barrier layer. <i>Journal of the Korean Physical Society</i> , 2016, 68, 306-310.	0.7	2
85	A tantalum diffusion barrier layer for improving the output performance of AlGaInP-based light-emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 032102.	1.5	2
86	Formation of Flexible and Transparent Indium Gallium Zinc Oxide/Ag/Indium Gallium Zinc Oxide Multilayer Film. <i>Journal of Electronic Materials</i> , 2016, 45, 4265-4269.	2.2	8
87	Control of refractive index by annealing to achieve high figure of merit for TiO ₂ /Ag/TiO ₂ multilayer films. <i>Ceramics International</i> , 2016, 42, 14071-14076.	4.8	24
88	Electrical Characteristics of Schottky Contacts to p-Type (001) GaP: Understanding of Carrier Transport Mechanism. <i>Journal of Electronic Materials</i> , 2016, 45, 5297-5301.	2.2	1
89	Highly flexible Al-doped ZnO/Ag/Al-doped ZnO multilayer films deposited on PET substrates at room temperature. <i>Ceramics International</i> , 2016, 42, 3473-3478.	4.8	31
90	Flexible and transparent TiO ₂ /Ag/ITO multilayer electrodes on PET substrates for organic photonic devices. <i>Journal of Materials Research</i> , 2015, 30, 1593-1598.	2.6	11

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91	Design of near-unity transmittance dielectric/Ag/ITO electrodes for GaN-based light-emitting diodes. <i>Current Applied Physics</i> , 2015, 15, 833-838.	2.4	19
92	Ultrafast chemical lithiation of single crystalline silicon nanowires: in situ characterization and first principles modeling. <i>RSC Advances</i> , 2015, 5, 17438-17443.	3.6	11
93	Optimization of transmittance and resistance of indium gallium zinc oxide/Ag/indium gallium zinc oxide multilayer electrodes for photovoltaic devices. <i>Current Applied Physics</i> , 2015, 15, 452-455.	2.4	18
94	Highly Transparent and Low-Resistance Indium-Free ZnO/Ag/ZnO Multilayer Electrodes for Organic Photovoltaic Devices. <i>Journal of Electronic Materials</i> , 2015, 44, 3967-3972.	2.2	24
95	Highly flexible ZnO/Ag/ZnO conducting electrode for organic photonic devices. <i>Ceramics International</i> , 2015, 41, 7146-7150.	4.8	42
96	Dependence of optical and electrical properties on Ag thickness in TiO ₂ /Ag/TiO ₂ multilayer films for photovoltaic devices. <i>Ceramics International</i> , 2015, 41, 8059-8063.	4.8	37
97	ITO-free inverted organic solar cells fabricated with transparent and low resistance ZnO/Ag/ZnO multilayer electrode. <i>Current Applied Physics</i> , 2015, 15, 829-832.	2.4	17
98	Embedment of nano-sized Ag layer into Ag-doped In ₂ O ₃ films for use as highly transparent and conductive anode in organic solar cells. <i>Applied Surface Science</i> , 2015, 347, 88-95.	6.1	13
99	Al-doped ZnO/Ag/Al-doped ZnO multilayer films with a high figure of merit. <i>Ceramics International</i> , 2015, 41, 14805-14810.	4.8	35
100	Formation of low resistance Ti/Al-based ohmic contacts on (11 $\bar{1}$ 2) semipolar n-type GaN. <i>Journal of Alloys and Compounds</i> , 2015, 652, 167-171.	5.5	8
101	Improving performance of high-power indium gallium nitride/gallium nitride-based vertical light-emitting diodes by employing simple n-type electrode pattern. <i>Materials Science in Semiconductor Processing</i> , 2015, 31, 209-213.	4.0	3
102	Optimizing n-type contact design and chip size for high-performance indium gallium nitride/gallium nitride-based thin-film vertical light-emitting diode. <i>Materials Science in Semiconductor Processing</i> , 2015, 31, 153-159.	4.0	18
103	Realization of highly transparent and low resistance TiO ₂ /Ag/TiO ₂ conducting electrode for optoelectronic devices. <i>Ceramics International</i> , 2015, 41, 3064-3068.	4.8	31
104	Investigation of Fermi level pinning at semipolar (11 $\bar{1}$ 2) p-type GaN surfaces. <i>Superlattices and Microstructures</i> , 2015, 77, 76-81.	3.1	14
105	Morphological stability of Ag reflector for high-power GaN-based vertical light-emitting diode by addition of Ni layer. <i>Superlattices and Microstructures</i> , 2014, 73, 342-349.	3.1	8
106	Controlling interface oxygen for forming Ag ohmic contact to semi-polar (11 $\bar{1}$ 2) plane p-type GaN. <i>Superlattices and Microstructures</i> , 2014, 75, 962-967.	3.1	2
107	Control of the preferred orientations of Cu(In,Ga)Se ₂ films and the photovoltaic conversion efficiency using a surface-functionalized molybdenum back contact. <i>Progress in Photovoltaics: Research and Applications</i> , 2014, 22, 69-76.	8.1	27
108	Polarity dependence of the electrical characteristics of Ag reflectors for high-power GaN-based light emitting diodes. <i>Applied Physics Letters</i> , 2014, 104, 172104.	3.3	3

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109	Electrical properties of CIGS/Mo junctions as a function of MoSe ₂ orientation and Na doping. Progress in Photovoltaics: Research and Applications, 2014, 22, 90-96.	8.1	61
110	Delayed π texture for improving the thermal stability of Ag reflectors for high-performance GaN-based light-emitting diodes. Scripta Materialia, 2014, 80, 5-8.	5.2	9
111	Highly thermally stable Pd/Zn/Ag ohmic contact to Ga-face p-type GaN. Journal of Alloys and Compounds, 2014, 588, 327-331.	5.5	13
112	Effect of a Mo back contact on Na diffusion in CIGS thin film solar cells. Progress in Photovoltaics: Research and Applications, 2013, 21, 58-63.	8.1	69
113	Growth behavior of cubic boron nitride (cBN) phase in B-C-N film deposited on Si substrate with non-uniform ion flux. Metals and Materials International, 2013, 19, 591-595.	3.4	1
114	Effect of an In layer on the thermal stability of Ag reflector for vertical GaN-based light-emitting diodes. Superlattices and Microstructures, 2013, 56, 77-85.	3.1	14
115	Silver-induced activation for improving the electrical characteristics of GaN-based vertical light-emitting diodes. Current Applied Physics, 2013, 13, 377-380.	2.4	2
116	Dependence of thickness and temperature on the thermal stability of Ag films deposited on GaN layers for vertical-geometry GaN-based light-emitting diodes. Superlattices and Microstructures, 2013, 61, 160-167.	3.1	4
117	Optical, electrical, and structural properties of ZrON/Ag/ZrON multilayer transparent conductor for organic photovoltaics application. Superlattices and Microstructures, 2013, 62, 119-127.	3.1	14
118	Improving the output power of near-ultraviolet InGaN/GaN-based light emitting diodes by enhancing the thermal and electrical properties of Ag-based reflector. Superlattices and Microstructures, 2013, 64, 7-14.	3.1	4
119	Realizing the Potential of ZnO with Alternative Non-Metallic Co-Dopants as Electrode Materials for Small Molecule Optoelectronic Devices. Advanced Functional Materials, 2013, 23, 3645-3652.	14.9	26
120	Effect of Different Quantum Well Structures on the Output Power Performance of GaN-Based Light-Emitting Diodes. Journal of Electronic Materials, 2013, 42, 2876-2880.	2.2	1
121	Effect of deposition temperature on cubic boron nitride thin film deposited by unbalanced magnetron sputtering method with a nanocrystalline diamond buffer layer. Metals and Materials International, 2013, 19, 1323-1326.	3.4	6
122	Plasmonic Au nanoparticles on 80 nm TiO ₂ nanotubes for enhanced photocatalytic water splitting. Journal of Renewable and Sustainable Energy, 2013, 5, .	2.0	17
123	Superhydrophilic Transparent Titania Films by Supersonic Aerosol Deposition. Journal of the American Ceramic Society, 2013, 96, 1596-1601.	3.8	31
124	Highly reliable Ag/Zn/Ag ohmic reflector for high-power GaN-based vertical light-emitting diode. Optics Express, 2012, 20, 19194.	3.4	21
125	Nanostructure Ag dots for improving thermal stability of Ag reflector for GaN-based light-emitting diodes. Applied Physics Letters, 2012, 101, 021115.	3.3	8
126	Improved light output power of GaN-based flip-chip light-emitting diode through SiO ₂ cones. Electronic Materials Letters, 2012, 8, 549-552.	2.2	9

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127	Ga Ordering and Electrical Conductivity in Nanotwin and Superlattice-Structured Ga-Doped ZnO. Crystal Growth and Design, 2012, 12, 1167-1172.	3.0	20
128	Improved efficiency of InGaN/GaN-based multiple quantum well solar cells by reducing contact resistance. Superlattices and Microstructures, 2012, 52, 299-305.	3.1	12
129	Enhanced thermal stability of Ag ohmic reflector for InGaN/GaN light-emitting diode using a Ru capping layer. Superlattices and Microstructures, 2012, 52, 357-363.	3.1	3
130	Improving the thermal stability of Ag Ohmic contacts for GaN-based vertical light-emitting diodes with a Cu capping layer. Journal of the Korean Physical Society, 2012, 60, 857-861.	0.7	0
131	Tuning Hydrophobicity with Honeycomb Surface Structure and Hydrophilicity with CF_4 Plasma Etching for Aerosol-Deposited Titania Films. Journal of the American Ceramic Society, 2012, 95, 3955-3961.	3.8	16
132	Fabrication of Patterned Magnetic Nanomaterials for Data Storage Media. Jom, 2012, 64, 1165-1173.	1.9	5
133	Electrical Characteristics of Ti/Al Ohmic Contacts to Molecular Beam Epitaxy-Grown N-polar n-type GaN for Vertical-Structure Light-Emitting Diodes. Journal of Electronic Materials, 2012, 41, 2145-2150.	2.2	1
134	Low-resistance Cr/Al Ohmic contacts to N-polar n-type GaN for high-performance vertical light-emitting diodes. Current Applied Physics, 2012, 12, 225-227.	2.4	3
135	Improved light output power of GaN-based light-emitting diodes by using Ag grids. Microelectronic Engineering, 2012, 95, 10-13.	2.4	3
136	Effect of TiO ₂ nanopatterns on the performance of hydrogenated amorphous silicon thin-film solar cells. Thin Solid Films, 2012, 520, 6287-6290.	1.8	1
137	Highly Reliable Ohmic Contacts to N-Polar n-Type GaN for High-Power Vertical Light-Emitting Diodes. IEEE Photonics Technology Letters, 2011, 23, 1784-1786.	2.5	5
138	Highly self-assembled nanotubular aluminum oxide by hard anodization. Journal of Materials Research, 2011, 26, 186-193.	2.6	16
139	Improved Electrostatic Discharge Protection in GaN-Based Vertical Light-Emitting Diodes by an Internal Diode. IEEE Photonics Technology Letters, 2011, 23, 423-425.	2.5	3
140	Preparation and characterization of electro-spun RuO ₂ -Ag ₂ O composite nanowires for electrochemical capacitors. Journal of Alloys and Compounds, 2011, 509, 4336-4340.	5.5	29
141	Fabrication and Magnetic Properties of Nonmagnetic Ion Implanted Magnetic Recording Films for Bit-Patterned Media. IEEE Transactions on Magnetics, 2011, 47, 2532-2535.	2.1	6
142	Depth-resolved correlation between physical and electrical properties of stressed SiN _x gate insulator films. Journal of Electroceramics, 2011, 26, 63-67.	2.0	4
143	Electrical characteristics of Cu-doped In ₂ O ₃ /Sb-doped SnO ₂ ohmic contacts for high-performance GaN-based light-emitting diodes. Journal of Electroceramics, 2011, 27, 109-113.	2.0	4
144	Improved Light Output of GaN-Based Light-Emitting Diodes by Using AgNi Reflective Contacts. Journal of Electronic Materials, 2011, 40, 2173-2178.	2.2	0

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